



DATA SHEET

SEMICONDUCTOR

1N4448M

500 mW DO-34 Hermetically Sealed Glass Fast Switching Diodes



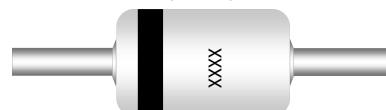
AXIAL LEAD
DO34

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

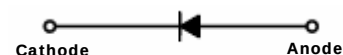
Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
T_{STG}	Storage Temperature Range	-65 to +200	$^\circ\text{C}$
T_J	Operating Junction Temperature	+175	$^\circ\text{C}$
W_{IV}	Working Inverse Voltage	75	V
I_O	Average Rectified Current	150	mA
I_{FM}	Non-repetitive Peak Forward Current	450	mA
I_{FSURGE}	Peak Forward Surge Current	2	A

These ratings are limiting values above which the serviceability of the diode may be impaired.

DEVICE MARKING DIAGRAM
(1N4448M)



Device Code : 1NxxxxM



ELECTRICAL SYMBOL

Specification Features:

- Fast Switching Device ($T_{RR} < 4.0 \text{ nS}$)
- DO-34 Package (JEDEC DO-204)
- Through-Hole Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- All external surfaces are corrosion resistant and leads are readily solderable
- Cathode indicated by polarity band

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
B_V	Breakdown Voltage	$I_R = 100\mu\text{A}$ $I_R = 5\mu\text{A}$	100 75		Volts
I_R	Reverse Leakage Current	$V_R = 20\text{V}$ $V_R = 75\text{V}$		25 5	nA μA
V_F	Forward Voltage 1N4448M 1N4448M	$I_F = 5\text{mA}$ $I_F = 100\text{mA}$	0.62	0.72 1.0	Volts
T_{RR}	Reverse Recovery Time	$I_F = I_R = 10\text{mA}$ $R_L = 100\Omega$ $I_{RR} = 1\text{mA}$		4	nS
C	Capacitance	$V_R = 0\text{V}$, $f = 1\text{MHz}$		4	pF

DEVICE CHARACTERISTICS

1N4448M

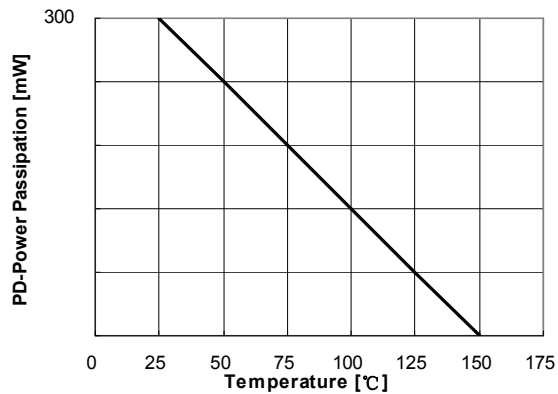


Figure 1. Power Dissipation vs Ambient Temperature
Valid provided leads at a distance of 0.8mm from case are kept at ambient temperature

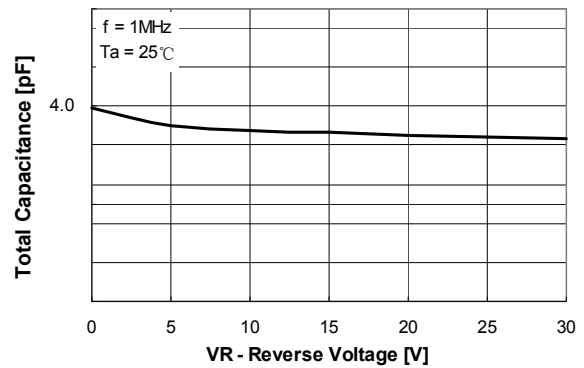


Figure 2. Total Capacitance

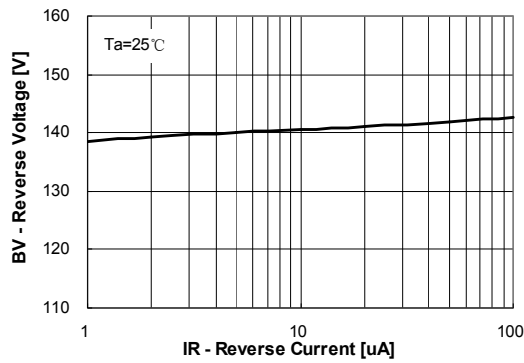


Figure 3. Reverse Voltage vs Reverse Current
BV – 1.0uA to 100uA

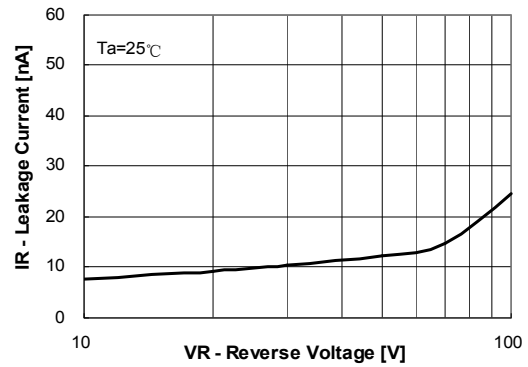


Figure 4. Reverse Current vs Reverse Voltage
IR – 10V to 100V

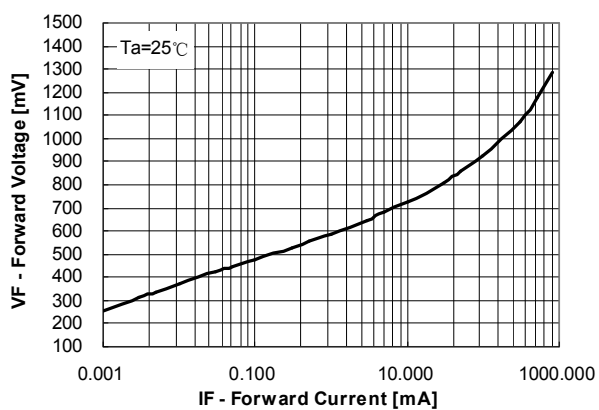


Figure 5. Forward Voltage vs Forward Current
VF – 0.001mA to 800mA

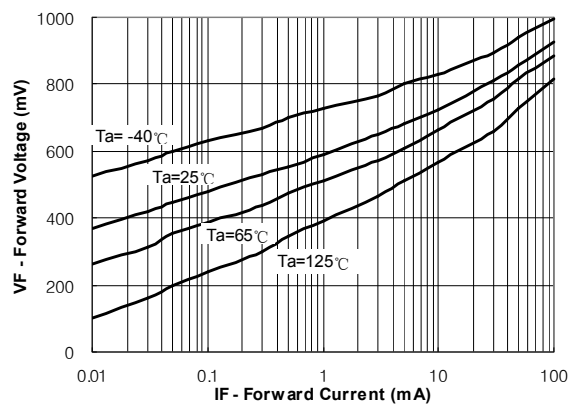


Figure 6. Forward Voltage vs Ambient Temperature
VF – 0.01mA to 100mA (-40 to +125 Deg C)